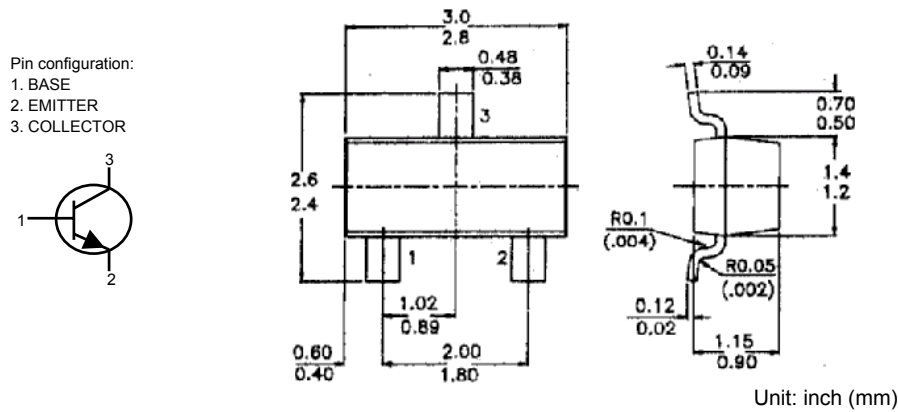


NPN Silicon Planar Epitaxial Transistors



Absolute Maximum Ratings

	Symbol	Value	UNIT
Collector-base voltage (open emitter)	V_{CBO}	max 75	V
Collector-emmitter voltage (open base)	V_{CEO}	max 40	V
Emmitter base voltage (open collector)	V_{EBO}	max 6.0	V
Collector current (d.c.)	I_C	max 600	mA
Total power dissipation up to $T_{amb} = 25^{\circ}C$	P_{tot}	max 250	mW
D.C. current gain $I_C = 150mA; V_{CE} = 10V$ $I_C = 500mA; V_{CE} = 10V$	h_{FE}	100 to 300 > 40	
Transition frequency at $f = 100MHz$ $I_C = 20mA; V_{CE} = 20V$	f_T	> 300	MHz

Ratings (at $T_A = 25^{\circ}C$ unless otherwise specified)

Limmiting values

	Symbol	Value	UNIT
Collector-base voltage (open emitter)	V_{CBO}	max 75	V
Collector-emitter voltage (open base)	V_{CEO}	max 40	V
Emitter-base voltage (open collector)	V_{EBO}	max 6.0	V
Collector current (d.c.)	I_C	max 600	mA
Total power dissipation up to $T_{amb} = 25^{\circ}C$	P_{tot}	max 250	mW
Storge Temperature	T_{stg}	-55 to +150	$^{\circ}C$
Junction Temperature	T_J	max 150	$^{\circ}C$
Thermal Resistance from junction to Ambient	$R_{th\ j-a}$	500	K/W

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Characteristics (at $T_j=25^\circ\text{C}$ unless otherwise specified)

	Symbol	Value	UNIT
Collector cut-off current $I_E = 0; V_{CB} = 60\text{V}$	I_{CBO}	< 0.01	μA
$I_E = 0; V_{CB} = 60\text{V}; T_j = 125^\circ\text{C}$	I_{CBO}	< 10	
$V_{EB} = 3\text{V}; V_{CE} = 60\text{V}$	I_{CEX}	< 10	nA
Base current with reverse biased emitter junction $V_{FB} = 3\text{V}; V_{CE} = 60\text{V}$	I_{BEX}	< 20	nA
Emitter-base cut-off current $I_C = 0; V_{EB} = 3\text{V}$	I_{EBO}	< 10	nA
Saturation voltage $I_C = 150\text{mA}; I_B = 15\text{mA}$	V_{CEsat}	< 300	mV
	V_{BEsat}	0.6 to 1.2	V
$I_C = 500\text{mA}; I_B = 50\text{mA}$	V_{CEsat}	< 1.0	V
	V_{BEsat}	< 2.0	V
Breakdown voltages $I_C = 1.0\text{mA}; I_B = 0$	$V_{(BR)CEO}$	> 40	V
$I_C = 100\mu\text{A}; I_E = 0$	$V_{(BR)CBO}$	> 75	
$I_C = 0; I_E = 10\mu\text{A}$	$V_{(BR)EBO}$	> 6.0	
D.C. current gain $I_C = 0.1\text{mA}; V_{CE} = 10\text{V}$	h_{FE}	> 35	
$I_C = 1\text{mA}; V_{CE} = 10\text{V}$		> 50	
$I_C = 10\text{mA}; V_{CE} = 10\text{V}$		> 75	
$I_C = 10\text{mA}; V_{CE} = 10\text{V}; T_{amb} = -55^\circ\text{C}$		> 35	
$I_C = 150\text{mA}; V_{CE} = 10\text{V}$		100 to 300	
$I_C = 150\text{mA}; V_{CE} = 1\text{V}$		> 50	
$I_C = 500\text{mA}; V_{CE} = 10\text{V}$		> 40	
Transition frequency at $f = 100\text{MHz}$ $I_C = 20\text{mA}; V_{CE} = 20\text{V}$	f_T	> 300	MHz
Output capacitance at $f = 1\text{MHz}$ $I_E = 0; V_{CB} = 10\text{V}$	C_O	< 8.0	pF
Input capacitance at $f = 1\text{MHz}$ $I_E = 0; V_{EB} = 0.5\text{V}$	C_i	< 25	pF
Noise figure at $R_S = 1\text{K ohm}$ $I_C = 100\mu\text{A}; V_{CE} = 10\text{V}; f = 1\text{kHz}$	F	< 4.0	dB

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Switching times (between 10% and 90% levels)			
Turn-on time switched to $I_C = 150\text{mA}$			
delay time	td	< 10	ns
rise time	tr	< 25	
Turn-off time switched from $I_C = 150\text{mA}$			
storage time	ts	< 225	
fall time	tf	< 60	